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N²O Processing Improves the 4H-SiC:SiO² Interface

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#	Paper	IF	Citations
158	Nitrogen passivation of deposited oxides on n 4H-SiC. <i>Applied Physics Letters</i> , 2002 , 81, 4266-4268	3.4	20
157	Development of high-current 4H-SiC ACCUFET. <i>IEEE Transactions on Electron Devices</i> , 2003 , 50, 471-478	2.9	14
156	Effects of Nitrogen Radical Irradiation on Performance of SiC MOSFETs. <i>Materials Science Forum</i> , 2003 , 433-436, 945-948	0.4	
155	Electrical and physical characterization of gate oxides on 4H-SiC grown in diluted N ₂ O. <i>Journal of Applied Physics</i> , 2003 , 93, 5682-5686	2.5	69
154	Thermal oxidation of (0001) 4H-SiC at high temperatures in ozone-admixed oxygen gas ambient. <i>Applied Physics Letters</i> , 2003 , 83, 884-886	3.4	7
153	Passivation of Oxide Layers on 4H-SiC Using Sequential Anneals in Nitric Oxide and Hydrogen. 2003 , 786, 811		1
152	4H-SiC Dmosfets for High Frequency Power Switching Applications. 2003 , 764, 1		5
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150	Enhancement of Inversion Channel Mobility in 4H-SiC MOSFETs using a Gate Oxide Grown in Nitrous Oxide (N ₂ O). <i>Materials Science Forum</i> , 2004 , 457-460, 1425-1428	0.4	13
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144	High Channel Mobilities of MOSFETs on Highly-Doped 4H-SiC (11-20) Face by Oxidation in N ₂ O Ambient. <i>Materials Science Forum</i> , 2004 , 457-460, 1429-1432	0.4	8
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